

62mm Half Bridge IGBT Module

DESCRIPTION :

- 1200V Trench / Field Stop Technology
- Low Switching Power Loss
- Positive Temperature Coefficient

TYPICAL APPLICATIONS :

- Variable-frequency Drive
- Servo
- UPS
- Inverter



$V_{CES}=1200V$, $I_{C\ nom}=300A$ / $I_{CRM}=600A$

IGBT, Inverter

MAXIMUM RATINGS

Characteristic	Condition	Symbol	Value	Unit
Collector- Emitter Voltage	$T_{vj}=25^{\circ}C$	V_{CES}	1200	V
Continuous DC collector current	$T_c=100^{\circ}C$, $T_{vj\ max}=175^{\circ}C$	$I_{C\ nom}$	300	A
Repetitive peak collector current	$t_p=1ms$	I_{CRM}	600	A
Gate emitter voltage		V_{GE}	± 20	V

ELECTRICAL CHARATERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter saturation voltage $V_{GE}=15V$, $I_C=300A$ $T_{vj}=25^{\circ}C$ $V_{GE}=15V$, $I_C=300A$ $T_{vj}=125^{\circ}C$ $V_{GE}=15V$, $I_C=300A$ $T_{vj}=150^{\circ}C$	$V_{CE(SAT)}$		2.00 2.45 2.60	2.50	V
Gate-Emitter threshold voltage $I_C=11.5mA$, $V_{GE}=V_{CE}$ $T_{vj}=25^{\circ}C$	$V_{GE(th)}$	5.3	5.9	6.5	V
Gate charge $V_{GE} = -15V \dots +15V$	Q_G		1.60		μC
Internal gate resistor	R_{Gint}		1.70		Ω
Input capacitance $f=1\ MHz$, $V_{CE}=25V$, $V_{GE}=0V$ $T_{vj}=25^{\circ}C$	C_{ies}		27.50		nF

Reverse transfer capacitance $f=1\text{ MHz}$, $V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$ $T_{vj}=25^\circ\text{C}$	C_{res}		0.85		nF
Collector-emitter cut-off current $V_{CE}=1200\text{V}$, $V_{GE}=0\text{V}$ $T_{vj}=25^\circ\text{C}$	I_{CES}			2	mA
Gate-emitter leakage current $V_{CE}=0\text{V}$, $V_{GE}=20\text{V}$ $T_{vj}=25^\circ\text{C}$	I_{GES}			200	nA
Turn-on delay time $I_C=300\text{A}$, $V_{CE}=600\text{ V}$ $T_{vj}=25^\circ\text{C}$ $V_{GE}=\pm 15\text{ V}$, $R_G=2\Omega$ $T_{vj}=125^\circ\text{C}$ (inductive load) $T_{vj}=150^\circ\text{C}$	$t_{d(ON)}$		185 194 194		ns
Rise time $I_C=300\text{A}$, $V_{CE}=600\text{ V}$ $T_{vj}=25^\circ\text{C}$ $V_{GE}=\pm 15\text{ V}$, $R_G=2\Omega$ $T_{vj}=125^\circ\text{C}$ (inductive load) $T_{vj}=150^\circ\text{C}$	t_r		48 52 54		ns
Turn-off delay time $I_C=300\text{A}$, $V_{CE}=600\text{ V}$ $T_{vj}=25^\circ\text{C}$ $V_{GE}=\pm 15\text{ V}$, $R_G=2\Omega$ $T_{vj}=125^\circ\text{C}$ (inductive load) $T_{vj}=150^\circ\text{C}$	$t_{d(OFF)}$		245 287 297		ns
Fall time $I_C=300\text{A}$, $V_{CE}=600\text{ V}$ $T_{vj}=25^\circ\text{C}$ $V_{GE}=\pm 15\text{ V}$, $R_G=2\Omega$ $T_{vj}=125^\circ\text{C}$ (inductive load) $T_{vj}=150^\circ\text{C}$	t_f		153 221 224		ns
Turn-on energy loss per pulse $I_C=300\text{A}$, $V_{CE}=600\text{ V}$ $T_{vj}=25^\circ\text{C}$ $V_{GE}=\pm 15\text{ V}$, $R_G=2.5\Omega$ $T_{vj}=125^\circ\text{C}$ $dv/dt = 5513\text{V}/\mu\text{s}$ ($T_{vj} = 150^\circ\text{C}$) $T_{vj}=150^\circ\text{C}$ (inductive load)	$E_{(ON)}$		13.00 26.90 31.40		mJ
Turn-off energy loss per pulse $I_C=300\text{A}$, $V_{CE}=600\text{ V}$ $T_{vj}=25^\circ\text{C}$ $V_{GE}=\pm 15\text{ V}$, $R_G=2.5\Omega$ $T_{vj}=125^\circ\text{C}$ $dv/dt = 5513\text{V}/\mu\text{s}$ ($T_{vj} = 150^\circ\text{C}$) $T_{vj}=150^\circ\text{C}$ (inductive load)	$E_{(OFF)}$		19.90 25.90 27.27		mJ
Short circuit (SC) data $V_{GE} \leq 15\text{ V}$, $V_{CE}=800\text{ V}$ $V_{CEmax}=V_{CES}-L_{sCE} \cdot di/dt$ $t_p \leq 10\mu\text{s}$, $T_{vj}=150^\circ\text{C}$	I_{SC}		927		A
Temperature under switching conditions	$T_{vj op}$	-40		150	$^\circ\text{C}$

Diode, Inverter**MAXIMUM RATINGS**

Characteristic	Condition	Symbol	Value	Unit
Repetitive peak reverse voltage	$T_{vj}=25^{\circ}\text{C}$	V_{RRM}	1200	V
Continuous DC forward current		I_F	300	A
Repetitive peak forward current	$t_p=1\text{ms}$	I_{FRM}	600	A
I^2t -value	$t_p=10\text{ms}$, $\sin 180^{\circ}$, $T_{vj}=125^{\circ}\text{C}$	I^2t	34848	A^2s

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward voltage $I_F=300\text{A}$, $V_{GE}=0\text{V}$ $T_{vj}=25^{\circ}\text{C}$ $I_F=300\text{A}$, $V_{GE}=0\text{V}$ $T_{vj}=125^{\circ}\text{C}$ $I_F=300\text{A}$, $V_{GE}=0\text{V}$ $T_{vj}=150^{\circ}\text{C}$	V_F		2.00 1.75 1.64	2.75	V
Peak reverse recovery current $I_F=300\text{A}$, $T_{vj}=25^{\circ}\text{C}$ $-diF/dt=4840\text{A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $T_{vj}=125^{\circ}\text{C}$ $V_R=600\text{V}$, $V_{GE}=-15\text{V}$ $T_{vj}=150^{\circ}\text{C}$	I_{RM}		256 339 358		A
Recovered charge $I_F=300\text{A}$, $T_{vj}=25^{\circ}\text{C}$ $-diF/dt=4840\text{A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $T_{vj}=125^{\circ}\text{C}$ $V_R=600\text{V}$, $V_{GE}=-15\text{V}$ $T_{vj}=150^{\circ}\text{C}$	Q_r		27.07 56.26 64.18		μC
Reverse recovered energy $I_F=300\text{A}$, $T_{vj}=25^{\circ}\text{C}$ $-diF/dt=4840\text{A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $T_{vj}=125^{\circ}\text{C}$ $V_R=600\text{V}$, $V_{GE}=-15\text{V}$ $T_{vj}=150^{\circ}\text{C}$	E_{rec}		11.54 22.01 24.23		mJ
Temperature under switching conditions	$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

Module

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Isolation test voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	V_{ISOL}		4000		V
Internal isolation			Al_2O_3		

Storage temperature	T_{STG}	-40		125	°C
Mounting torque for modul mounting	M	3		6	Nm
Weight	W		315		g

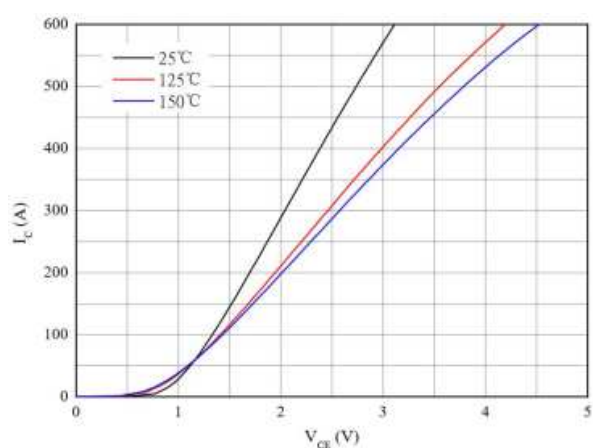


Figure 1. Typical output characteristics ($V_{GE}=15V$)

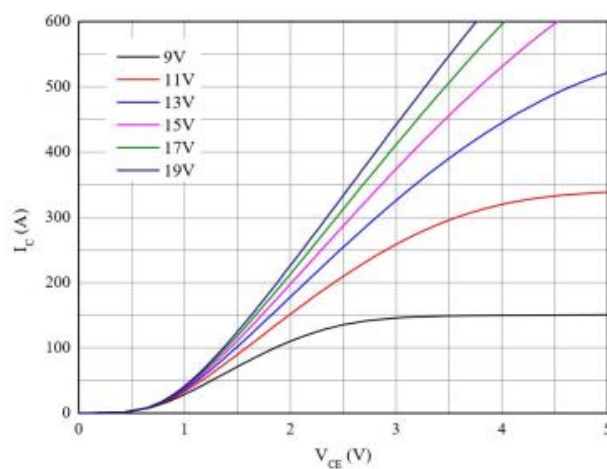


Figure 2. Typical output characteristics ($T_{vj}=150^{\circ}C$)

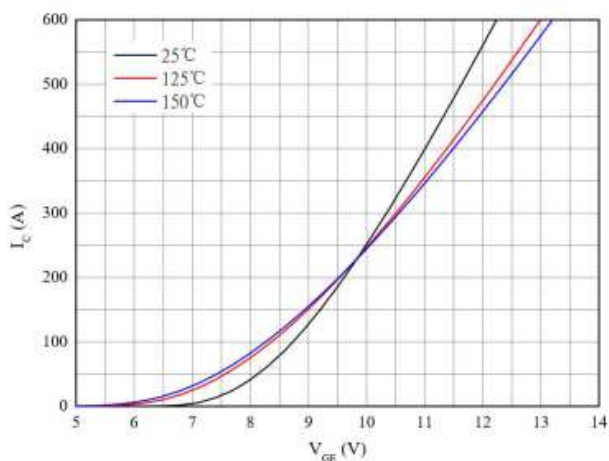


Figure 3. Typical transfer characteristic ($V_{CE}=20V$)

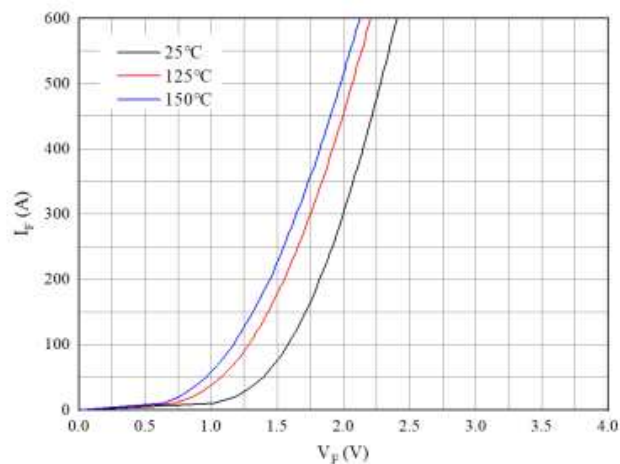


Figure 4. Forward characteristic of Diode

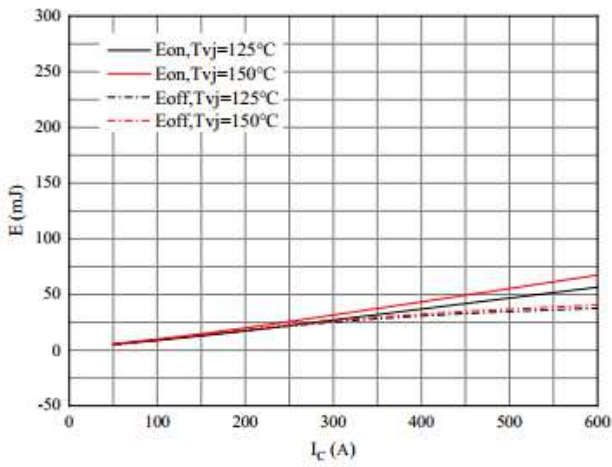


Figure 5. Switching losses of IGBT
VGE=± 15V, RGon=2Ω, RGoff=2Ω, VCE=600V

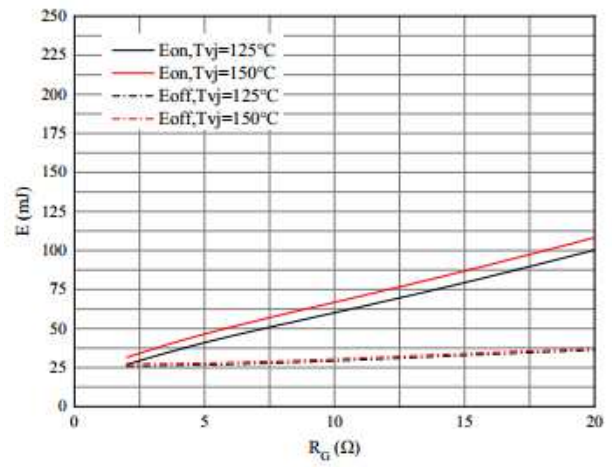


Figure 6. Switching losses of IGBT
VGE=± 15V, IC=300A, VCE=600V

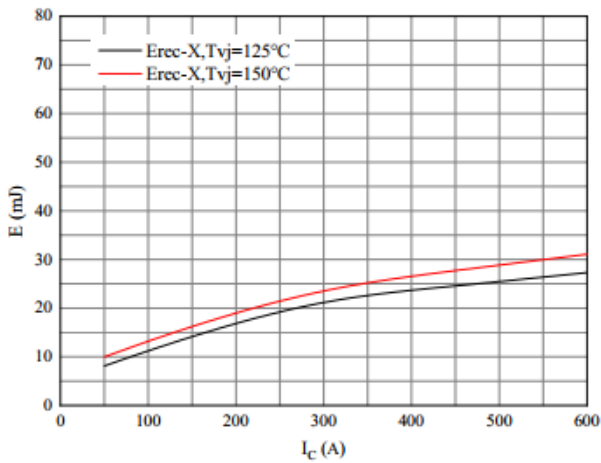


Figure 7. Switching losses of Diode
RGon=2Ω, VCE=600V

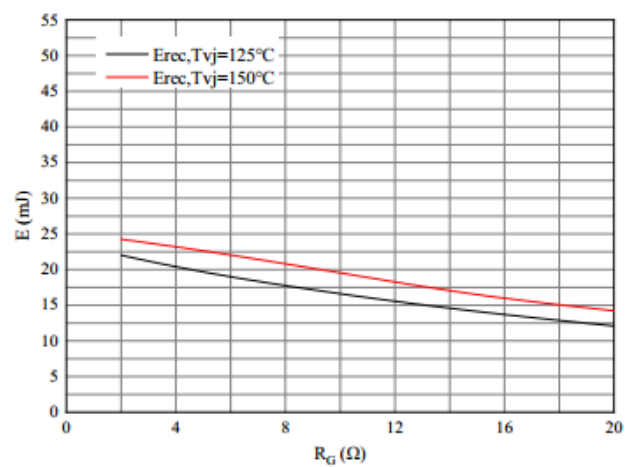


Figure 8. Switching losses of Diode
IF=300A, VCE=600V

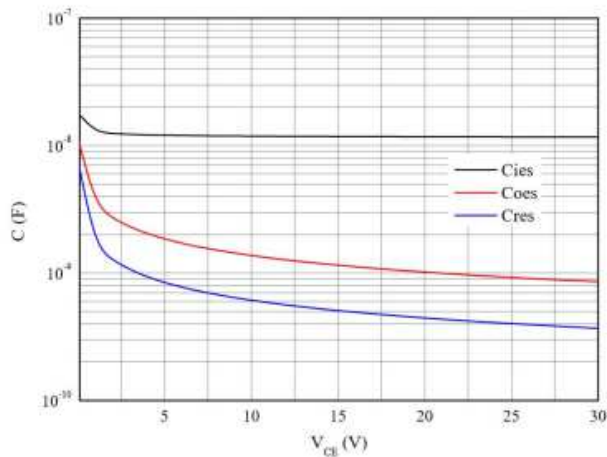


Figure 9. Capacitance characteristic

Notice

MOSPEC reserves the rights to make changes of the content herein the document anytime without notification. MOSPEC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies. Please refer to MOSPEC website for the last document.

MOSPEC disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially incurred.

Application shown on the herein document are examples of standard use and operation. Customers are responsible for comprehending suitable use in particular applications. MOSPEC makes no representation or warranty that such application will be suitable for the specified use without further testing or modification.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by MOSPEC for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of MOSPEC or others.

These MOSPEC products are intended for usage in general electronic equipment. Please make sure to consult with MOSPEC before you use these MOSPEC products in equipment which require specialized quality and/or reliability, and in equipment which could have major impact to the welfare of human life (atomic energy control, aeronautics , traffic control, combustion control, safety devices etc.)